TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

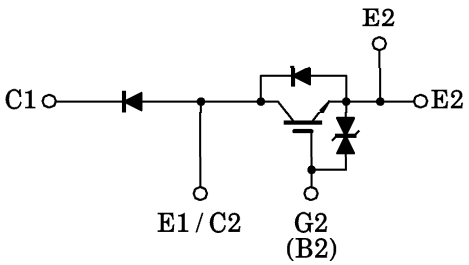
MG100Q1ZS40

HIGH POWER SWITCHING APPLICATIONS.

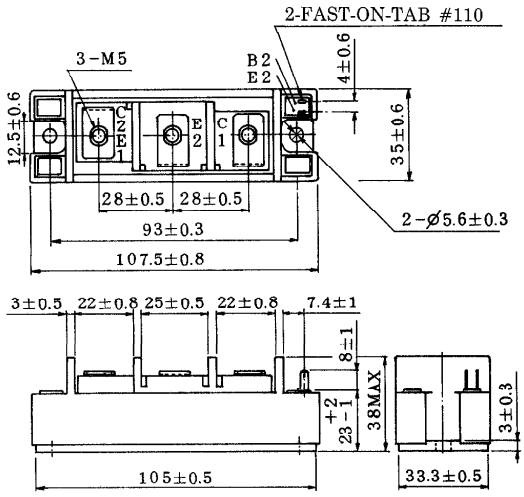
CHOPPER APPLICATIONS.

- High Input Impedance
- High Speed : $t_f = 0.5\mu s$ (Max.)
  $t_{rr} = 0.5\mu s$ (Max.)
- Low Saturation Voltage
  : $V_{CE\,(sat)} = 4.0V$ (Max.)
- Enhancement-Mode
- The Electrodes are Isolated from Case.

EQUIVALENT CIRCUIT



Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	2-108A3A

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collector Current	DC	I_C	100	A
	1ms	I_{CP}	200	
Forward Current	DC	I_F	100	A
	1ms	I_{FM}	200	
Collector Power Dissipation (Tc = 25°C)		P_C	670	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−40~125	°C
Isolation Voltage		V_{Isol}	2500 (AC 1 min.)	V
Screw Torque (Terminal / Mounting)		—	3 / 3	N·m

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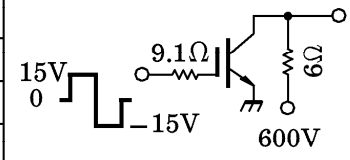
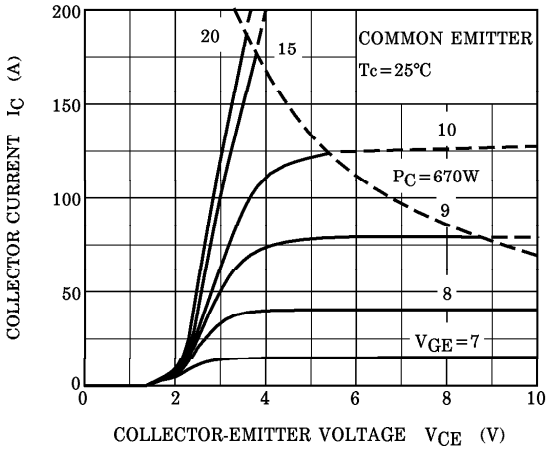
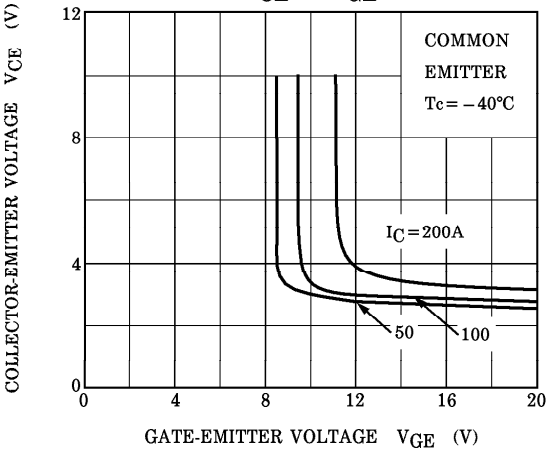
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V$, $V_{CE} = 0$	—	—	±10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V$, $V_{GE} = 0$	—	—	1.0	mA
Collector-Emitter Voltage		V_{CES}	$I_C = 1mA$, $V_{GE} = 0$	1200	—	—	V
Gate-Emitter Cut-off Voltage		$V_{GE\ (off)}$	$V_{CE} = 5V$, $I_C = 100mA$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE\ (sat)}$	$I_C = 100A$, $V_{GE} = 15V$	—	3.0	4.0	V
Input Capacitance		C_{ies}	$V_{CE} = 10V$, $V_{GE} = 0$ $f = 1MHz$	—	12000	—	pF
Switching Time	Rise Time	t_r		—	0.3	0.6	μs
	Turn-on Time	t_{on}		—	0.4	0.8	
	Fall Time	t_f		—	0.2	0.5	
	Turn-off Time	t_{off}		—	0.8	1.5	
Forward Voltage		V_F	$I_F = 100A$, $V_{GE} = 0$	—	2.0	3.0	V
Reverse Recovery Time		t_{rr}	$I_F = 100A$, $V_{GE} = -10V$ $di/dt = 200A/\mu s$	—	0.25	0.5	μs
Thermal Resistance	Transistor	$R_{th\ (j-c)}$	—	—	—	0.19	°C / W
	Diode			—	—	0.5	

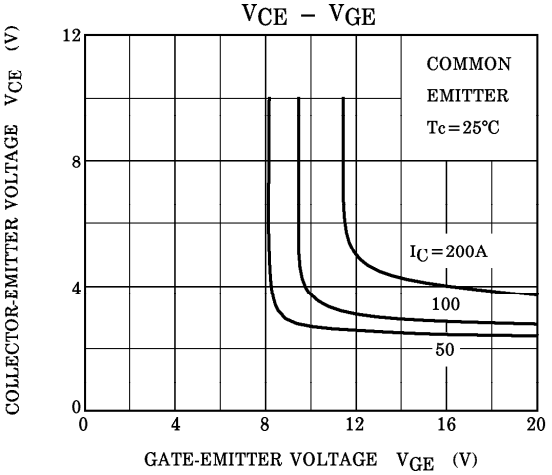
I_C – V_{CE}



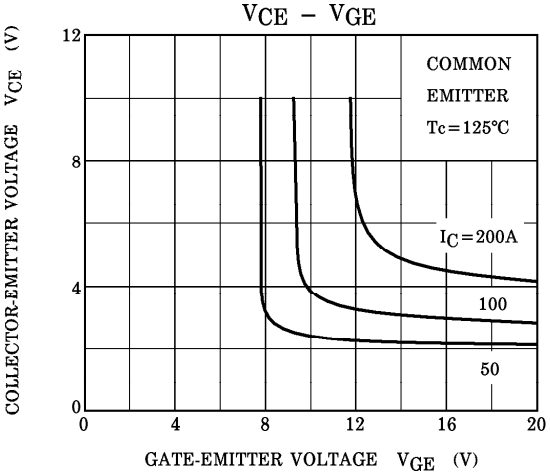
V_{CE} – V_{GE}



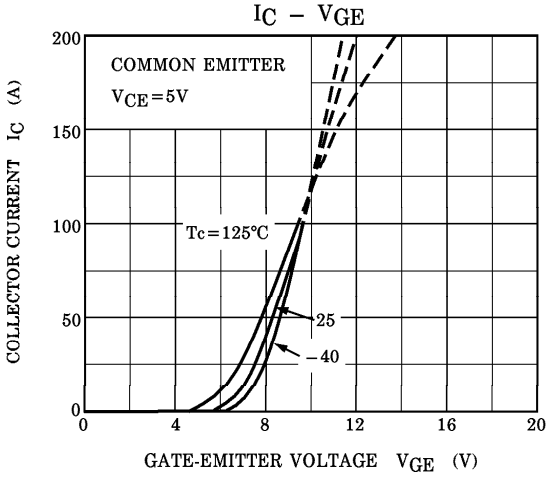
V_{CE} – V_{GE}



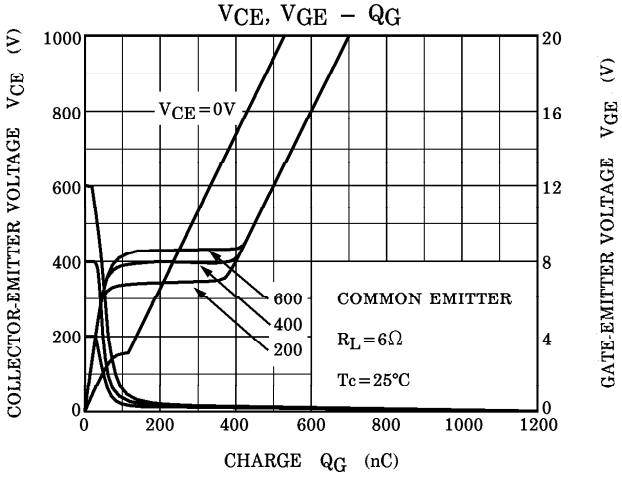
V_{CE} – V_{GE}



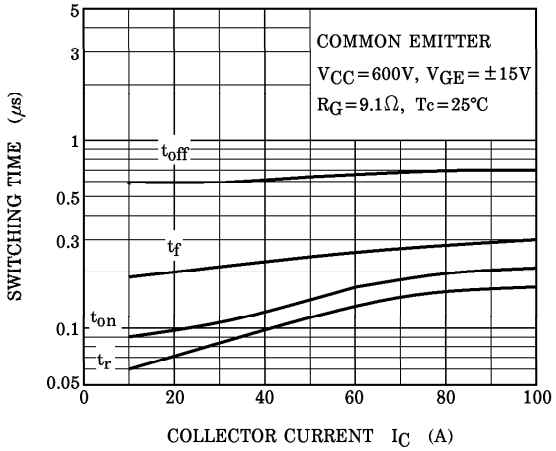
I_C – V_{GE}



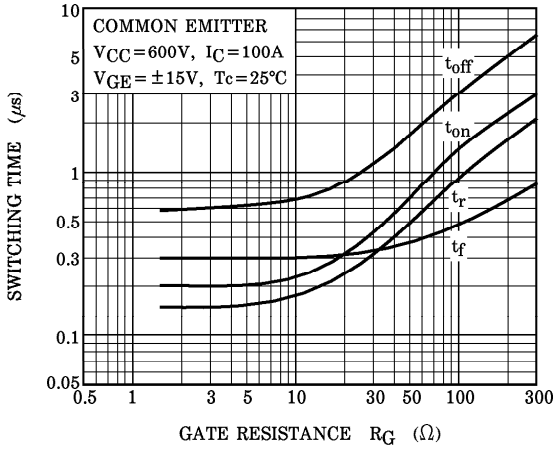
V_{CE}, V_{GE} – Q_G



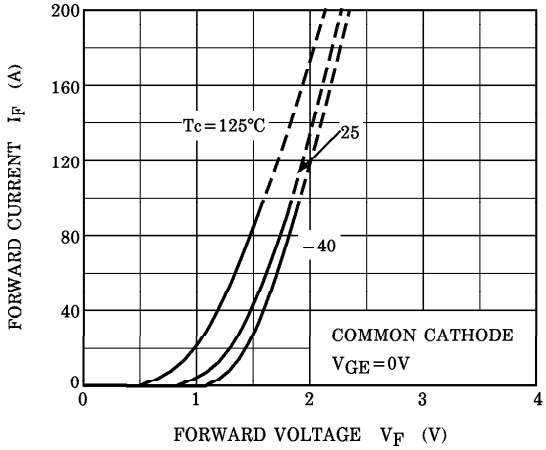
SWITCHING TIME – I_C



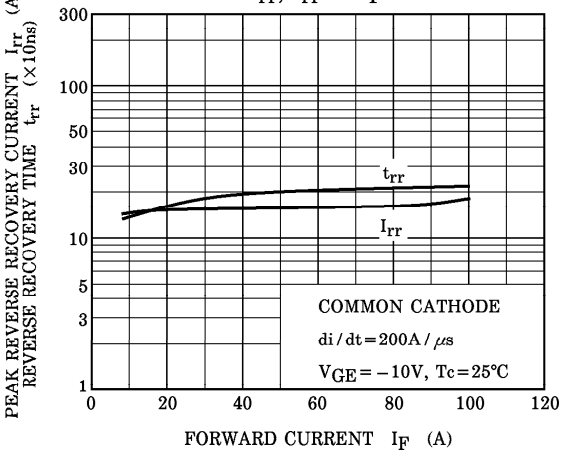
SWITCHING TIME – R_G



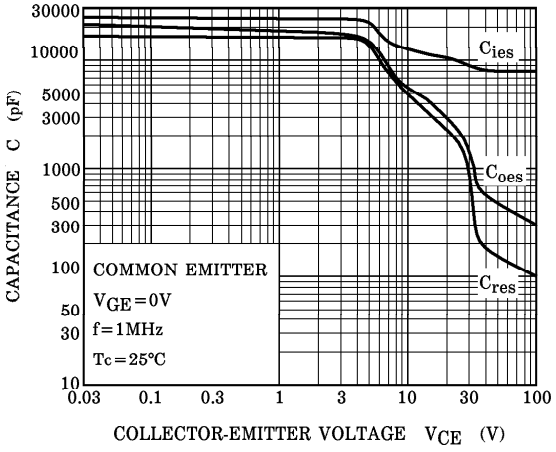
I_F – V_F



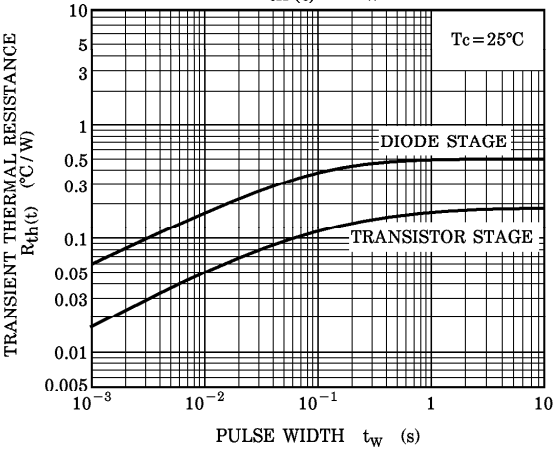
t_{rr}, I_{rr} – I_F



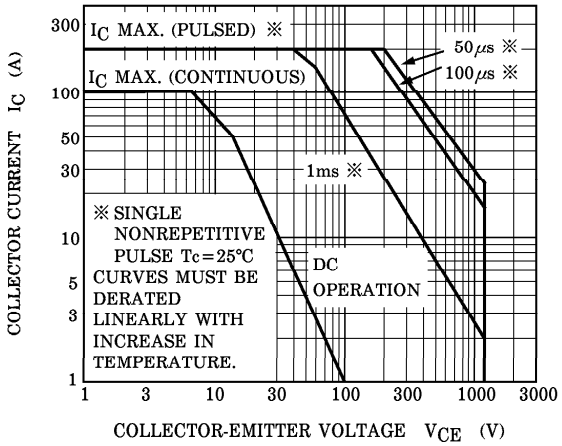
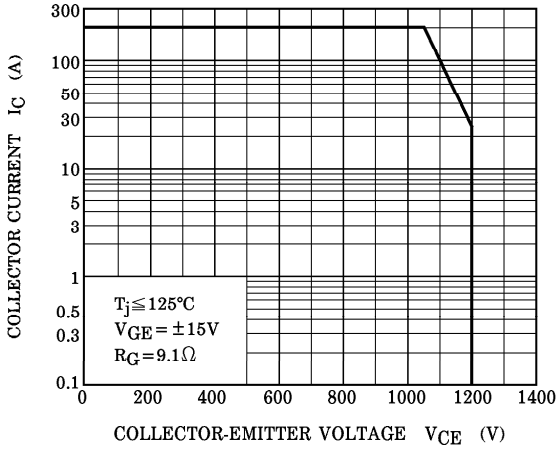
C – V_{CE}



$R_{th\,(t)}$ – t_w



SAFE OPERATING AREA



REVERSE BIAS SOA